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FDA18N50 N-Channel UniFET[™] MOSFET 500 V, 19 A, 265 mΩ

Features

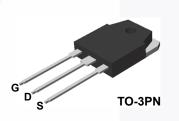
- $R_{DS(on)}$ = 265 m Ω (Max.) @ V_{GS} = 10 V, I_D = 9.5 A
- Low Gate Charge (Typ. 45 nC)
- Low C_{rss} (Typ. 25 pF)
- 100% Avalanche Tested

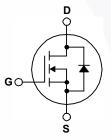
Applications

- PDP TV
- Uninterruptible Power Supply
- AC-DC Power Supply

Description

UniFETTM MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

| Symbol | | Parameter | | FDA18N50 | Unit | |
|----------------------------------|---|---|-------------|-------------|-----------|--|
| V _{DSS} | Drain-Source Voltage | | | 500 | V | |
| ID | Drain Current | - Continuous ($T_C = 25^{\circ}C$) - Continuous ($T_C = 100^{\circ}C$) | | 19 11.4 | A A | |
| I _{DM} | Drain Current | - Pulsed | (Note 1) | 76 | А | |
| V _{GSS} | Gate-Source voltage | | | ±30 | V | |
| E _{AS} | Single Pulsed Avalanche Energy | | (Note 2) | 945 | mJ | |
| I _{AR} | Avalanche Current | | (Note 1) | 19 | А | |
| E _{AR} | Repetitive Avalanche Energy | | (Note 1) | 23 | mJ | |
| dv/dt | Peak Diode Recovery dv/dt | | (Note 3) | 4.5 | V/ns | |
| P _D | Power Dissipation | (T _C = 25°C) - Derate above 25°C | | 239 1.92 | W W/°C | |
| T _{J,} T _{STG} | Operating and Storage Temperature Range | | -55 to +150 | °C | | |
| TL | Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds | | 300 | °C | | |

Thermal Characteristics

| Symbol | Parameter | FDA18N50 | Unit | |
|-----------------------|---|----------|------|--|
| $R_{	ext{	heta}JC}$ | Thermal Resistance, Junction-to-Case, Max. | 0.52 | °C/W | |
| $R_{	extsf{	heta}JA}$ | Thermal Resistance, Junction-to-Ambient, Max. | 40 | C/W | |

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| N-Channel UniFET ^{1M} MOSFET | Unit V V/°C μΑ μΑ nA nA N Ω S | |
|---------------------------------------|--|----|
| SFET | V Ω | |
| | | S |
| | | pF |
| | | pF |
| | | pF |

Package Marking and Ordering Information

| Device Marking | Device | Package | Reel Size | Tape Width | Quantity |
|----------------|----------|---------|-----------|------------|----------|
| FDA18N50 | FDA18N50 | TO-3PN | Tube | N/A | 30 units |

Electrical Characteristics $T_{C} = 25^{\circ}C$ unless otherwise noted.

| Symbol | Parameter Conditions | | Min. | Тур. | Max | Unit |
|---|---|---|------|-------|---------|----------|
| Off Charac | teristics | | | | | |
| BV _{DSS} | Drain-Source Breakdown Voltage | $V_{GS} = 0V, I_{D} = 250\mu A$ | | | | V |
| ΔBV _{DSS} / ΔT _J | Breakdown Voltage Temperature Coefficient | $I_D = 250\mu A$, Referenced to $25^{\circ}C$ | | 0.5 | | V/°C |
| I _{DSS} | Zero Gate Voltage Drain Current | $V_{DS} = 500V, V_{GS} = 0V$ $V_{DS} = 400V, T_{C} = 125^{\circ}C$ | | | 1 10 | μΑ μΑ |
| I _{GSSF} | Gate-Body Leakage Current, Forward | V _{GS} = 30V, V _{DS} = 0V | | | 100 | nA |
| I _{GSSR} | Gate-Body Leakage Current, Reverse | V _{GS} = -30V, V _{DS} = 0V | | | -100 | nA |
| On Charac | teristics | | | | | |
| V _{GS(th)} | Gate Threshold Voltage | $V_{DS} = V_{GS}, I_D = 250 \mu A$ | 3.0 | | 5.0 | V |
| R _{DS(on)} | Static Drain-Source On-Resistance | V _{GS} = 10V, I _D = 9.5A | | 0.220 | 0.265 | Ω |
| 9 _{FS} | Forward Transconductance | V _{DS} = 40V, I _D = 9.5A | | 25 | | S |
| Dynamic C | Characteristics | | | | 1 | |
| C _{iss} | Input Capacitance | V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz | | 2200 | 2860 | pF |
| C _{oss} | Output Capacitance | | | 330 | 430 | pF |
| C _{rss} | Reverse Transfer Capacitance | _ | | 25 | 40 | pF |
| Switching | Characteristics | | | | | |
| t _{d(on)} | Turn-On Delay Time | V _{DD} = 250V, I _D = 19A | | 55 | 120 | ns |
| t _r | Turn-On Rise Time | $R_{G} = 25\Omega$ | | 165 | 340 | ns |
| t _{d(off)} | Turn-Off Delay Time | | - | 95 | 200 | ns |
| t _f | Turn-Off Fall Time | (Note 4) | | 90 | 190 | ns |
| Qg | Total Gate Charge | V _{DS} = 400V, I _D = 19A | | 45 | 60 | nC |
| Q _{gs} | Gate-Source Charge | V _{GS} = 10V | | 12.5 | | nC |
| Q _{gd} | Gate-Drain Charge | (Note 4) | | 19 | | nC |
| Drain-Sour | rce Diode Characteristics and Maximur | n Ratings | | | | |
| I _S | Maximum Continuous Drain-Source Diode Forward Current | | | | 19 | Α |
| I _{SM} | Maximum Pulsed Drain-Source Diode Forward Current | | | | 76 | Α |
| V _{SD} | Drain-Source Diode Forward Voltage | V _{GS} = 0V, I _S = 19A | | | 1.4 | V |
| t _{rr} | Reverse Recovery Time | V _{GS} = 0V, I _S = 19A | | 500 | | ns |
| Q _{rr} | Reverse Recovery Charge | dI _F /dt =100A/μs | | 5.4 | | μC |

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature

2. L = 4.7mH, I_{AS} = 19A, V_DD = 50V, R_G = 25 Ω , Starting T_J = 25°C

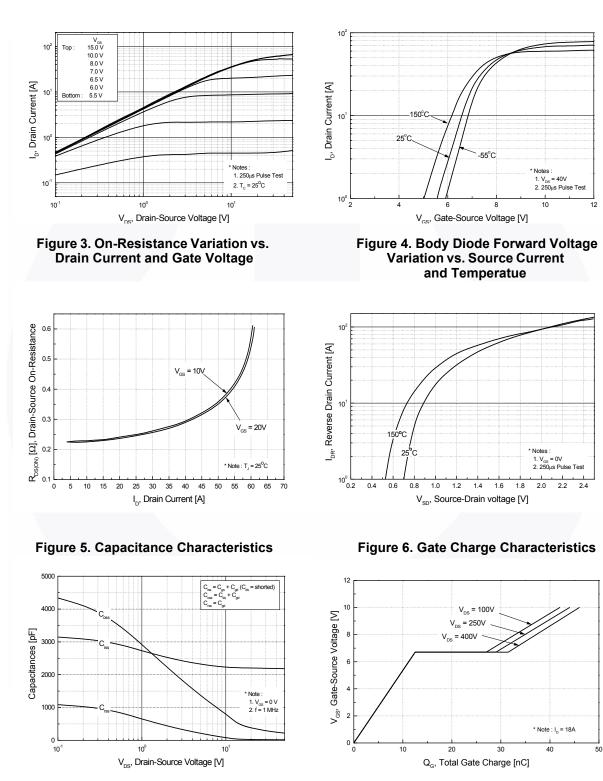
3. I_{SD} \leq 19A, di/dt \leq 200A/µs, V_{DD} \leq BV_{DSS}, Starting T_J = 25°C

4. Essentially Independent of Operating Temperature Typical Characteristics

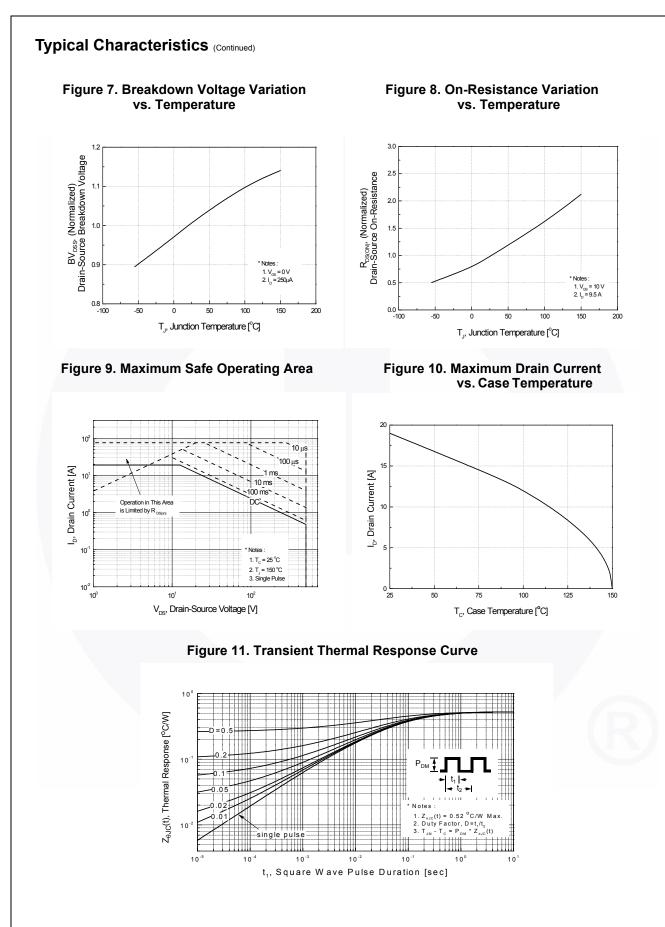
Typical Characteristics



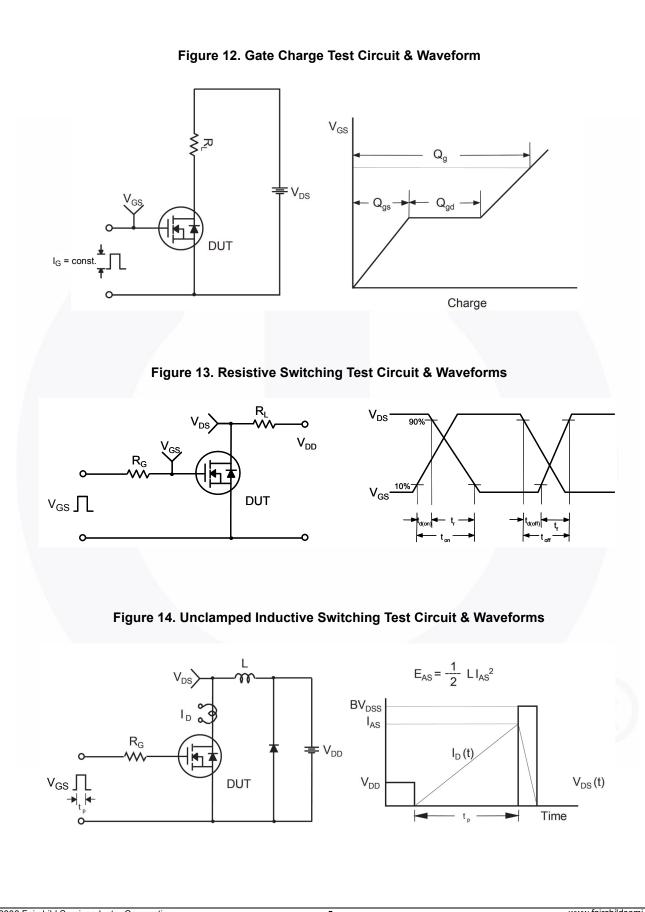
Figure 2. Transfer Characteristics



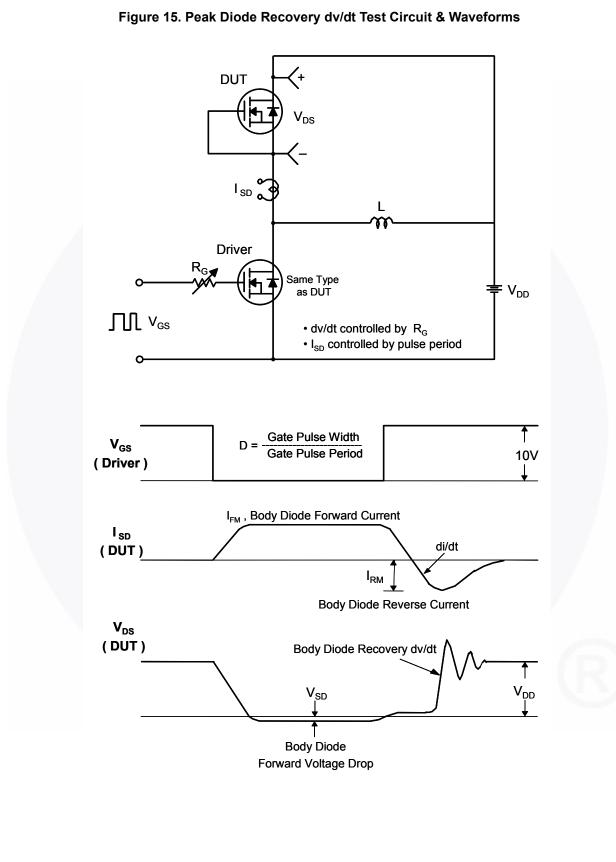
FDA18N50 — N-Channel UniFETTM MOSFET

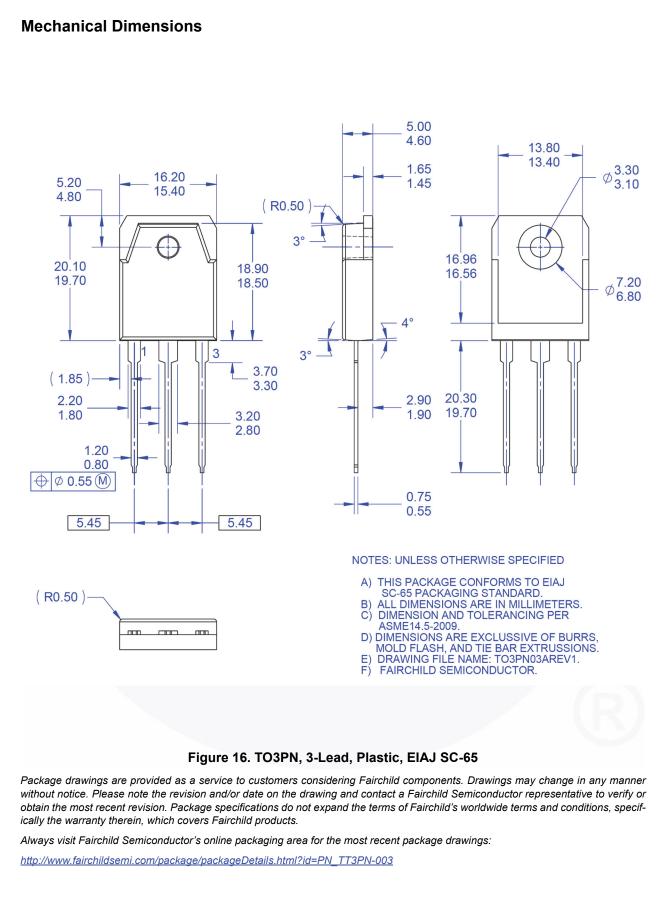


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